Supporting information

Modulation of electron-phonon coupling in one-dimensionally nanorippled graphene on a macrofacet of 6H-SiC

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Supporting figure:
Figure S1 STS modulation in a wide area

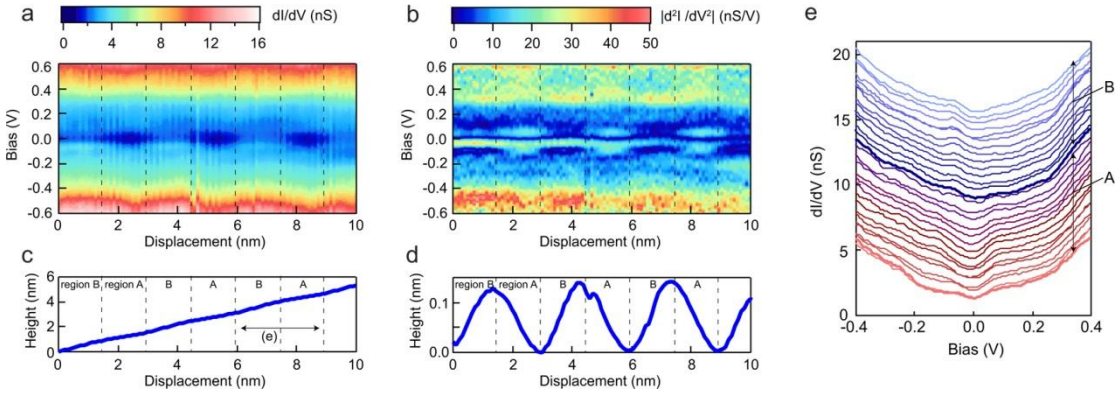

Figure S1 (a,b) *dI/dV* and $|d^2I/dV^2|$ spectra on a macrofacet shown as images on a 10 nm line of the [1-100] direction. In the regions A, dips of the *dI/dV* spectra at zero bias voltage are deeper than those in the regions B. The tip was fixed with the condition that the sample bias voltage was 0.6 V and the tunneling current was 3.0 nA. (c, d) Height profiles of the macrofacet area where the spectra were measured. In (c) the horizontal axis is parallel to the SiC(0001) terrace while in (d) it is parallel to the macrofacet face. (e) Line plots of a part of the *dI/dV* spectra.